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| INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i> | Docket Number (Optional) NSC1-M3300 [P05678] | Application Number New |
| | Applicant(s) Charles Dark et al.. | |
| | Filing Date Herewith | Group Art Unit Unknown |

U.S. PATENT DOCUMENTS

| *EXAMINER INITIAL | REF | DOCUMENT NUMBER | DATE | NAME | CLASS | SUBCLASS | FILING DATE |
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FOREIGN PATENT DOCUMENTS

| | REF | DOCUMENT NUMBER | DATE | COUNTRY | CLASS | SUBCLASS | TRANSLATION | |
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OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

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| WL | A | "The Effects of Fluorine on Parametrics and Reliability in a 0.18-µm 3.5/6.8 nm Dual Gate Oxide CMOS Technology"; | | | | | |
| WL | | Terence B. Hook et al.; IEEE Transactions on Electron Devices, Vol. 48, No. 7, July 2001; pp 1346-1353 | | | | | |
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| Examiner <i>W. H. Z. Smith</i> | Date Considered <i>6/23/04</i> |
| Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. | |